

APPLICATIONS

MMG75S170B6TC

MODULE CHARACTERISTICS (T_c=25°C unless otherwise specified)

Symbol	Parameter/Test Conditions		Values	Unit
T _{Jmax}	Max. Junction Temperature		175	
T _{Jop}	Operating Temperature		-40~150	
T _{stg}	Storage Temperature		-40~125	
V _{isol}	Isolation Breakdown Voltage	AC, 50Hz(R.M.S), t=1minute	4000	V
CTI	Comparative Tracking Index		· 200	
Torque	to heatsink	Recommended \ddot{A} M6 \ddot{A}	3~5	Nm
	to terminal	Recommended \ddot{A} M5 \ddot{A}	2.5~5	Nm
Weight			160	g

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I_F (A)

E_{REC} (mJ)

V_F (V)

Figure 9. Diode Forward Characteristics Diode -inverter

R_g (Å Å)

Figure 10. Switching Energy vs Gate Resistor Diode inverter

nm

Figure 13. Circuit Diagram

Dimensions in (mm)
Figure 14. Package Outline